

CLAIMS

1. A ceramic substrate for a
semiconductor-producing/examining device having a conductor
5 formed on a surface of the ceramic substrate or inside the ceramic
substrate,
wherein:
said substrate is made of a non-oxide ceramic containing
oxygen; and
10 the pore diameter of the maximum pore thereof is 50 μm
or less.
2. The ceramic substrate for the
semiconductor-producing/examining device according to claim 1,
15 wherein said non-oxide ceramic is a nitride ceramic.
3. The ceramic substrate for the
semiconductor-producing/examining device according to claim 1,
20 wherein said non-oxide ceramic is a carbide ceramic.
4. The ceramic substrate for the
semiconductor-producing/examining device according to any of
claims 1 to 3,
wherein said ceramic substrate contains oxygen in an amount
25 of 0.05 to 10% by weight.
5. The ceramic substrate for the
semiconductor-producing/examining device according to any of
claims 1 to 4,
30 wherein said ceramic substrate has a porosity of 5% or
less.
6. The ceramic substrate for the
semiconductor-producing/examining device according to any of
35 claims 1 to 5,

wherein said ceramic substrate is used within the temperature range of 100 to 700 °C.

7. The ceramic substrate for the
5 semiconductor-producing/examining device according to any of claims 1 to 6,

wherein said ceramic substrate has a thickness of 25 mm or less, and a diameter of 200 mm or more.

- 10 8. The ceramic substrate for the semiconductor-producing/examining device according to any of claims 1 to 7,

wherein said ceramic substrate has a plurality of through holes into which lifter pins for a semiconductor wafer will be

- 15 inserted.

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